

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	IS&R	L1	2027	(257/391,392,402,403,408).CCLS.	US-PGPUB; USPAT; EPO; DERWE NT	2006/06/07 14:33
2	BRS	L2	77	1 and ("threshold adjustment" "threshold adjust" "threshold adjusting")	US-PGPUB; USPAT; EPO; DERWE NT	2006/06/07 14:41
3	BRS	L3	45	2 and (ldd "lightly doped drain")	US-PGPUB; USPAT; EPO; DERWE NT	2006/06/07 14:41
4	BRS	L5	45	3 and @ad<"20031020"	US-PGPUB; USPAT; EPO; DERWE NT	2006/06/07 14:41
5	BRS	L6	6	5 and (gate "gate electrode") near5 (hole aperture opening)	US-PGPUB; USPAT; EPO; DERWE NT	2006/06/07 14:41
6	BRS	L7	145548	(fet "field effect transistor")	US-PGPUB; USPAT; EPO; DERWE NT	2006/06/07 14:46

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L9	5440	7 and (gate "gate electrode") near5 (hole aperture opening)	US-PGPUB; USPAT; EPO; DERWE NT	2006/06/07 14:46
8	BRS	L10	95	9 and ("threshold adjustment" "threshold adjust" "threshold adjusting")	US-PGPUB; USPAT; EPO; DERWE NT	2006/06/07 14:41
9	BRS	L11	43	10 and (ldd "lightly doped drain")	US-PGPUB; USPAT; EPO; DERWE NT	2006/06/07 14:47
10	BRS	L13	40	11 and @ad<"20031020"	US-PGPUB; USPAT; EPO; DERWE NT	2006/06/07 14:47
11	BRS	L14	68388	(tft "thin film transistor")	US-PGPUB; USPAT; EPO; DERWE NT	2006/06/07 14:46
12	BRS	L15	4060	14 and (gate "gate electrode") near5 (hole aperture opening)	US-PGPUB; USPAT; EPO; DERWE NT	2006/06/07 14:46

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L16	798	15 and (ldd "lightly doped drain")	US-PGPUB; USPAT; EPO; DERWE NT	2006/06/07 14:47
14	BRS	L17	571	16 and @ad<"20031020"	US-PGPUB; USPAT; EPO; DERWE NT	2006/06/07 14:47
15	BRS	L18	0	17 and (hole aperture opening) near5 ("channel implant" "channel implanting" "channel implantation")	US-PGPUB; USPAT; EPO; DERWE NT	2006/06/07 14:48
16	BRS	L19	8	17 and ("channel implant" "channel implanting" "channel implantation")	US-PGPUB; USPAT; EPO; DERWE NT	2006/06/07 14:49